

Specification for Approval

DEVICE NUMBER: BIR-BO13J4C-1

SAMPLES ATTACHED AREA

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2015/7/7	1.0	1.0	1.0	1.0	1.0				Initial Released
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FOR CUSTOMER'S APPROVAL STAMP OR SIGNATURE

APPROVED	PURCHASE	MANUFACTURE	QUALITY	ENGINEERING

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ISSUED	APPROVED	PREPARED		
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2015.07.07	2015.07.07	2015.07.07		
孝 嚴	初 榮	銳 明		



BIR-BO13J4C-1

END-LOOK PACKAGE LIGHT EMITTING DIODE

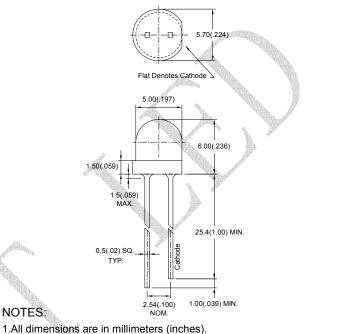
Features:

- 1. High radiant power and high radiant intensity.
- 2. Standard T-1package.
- 3. Peak wavelength λp=850nm.
- 4. Good spectral matching to Si- photo detector.
- 5. Radiant angle: 55°
- 6. Lens Appearance: Water Clear.
- 7. This product doesn't contain restriction substance, comply ROHS standard

Applications:

- 1. Remote Control.
- 2. Automatic Control System.

Package Dimensions:



- 2. Tolerance is ±0.25mm (0.01') unless otherwise specified.
- 3.Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit	
Power Dissipation	Pd	180	mW	
Continuous Forward Current	I _F	100	mA	
Peak Forward Current *1	I _{FP}	1.0	А	
Reverse Voltage	V _R	5	V	
Operating Temperature	Topr	-40°C ~85°C	-	
Storage Temperature	Tstg	-45°C ~85°C	-	

⁽³⁰⁰pps 10us pulse)

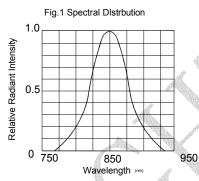


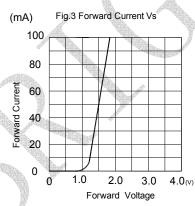
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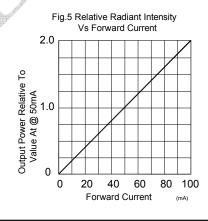
Optical- Electrical Characteristics (@T_A=25℃)

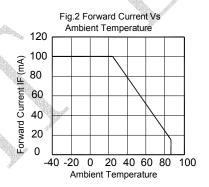
Parameter	Symbol	Test Conditions	Min	TYP	Max	Unit
Radiant Intensity	le	I _F =50mA	7.07	20		mW/sr
Forward Voltage	V _F	I _F =50mA		1.5	1.8	V
Reverse Current	I _R	V _R =5V		-	100	μA
Peak Wavelength	λр	I _F =50mA		850		nm
Spectral Line Half- Width	Δλ	I _F =50mA	-	50)-\	nm
Viewing Angle	2θ _{1/2}	I _F =20mA		55		deg

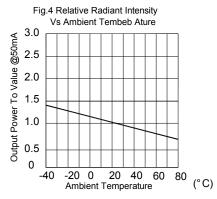
Typical Optical-Electrical Characteristic Curves

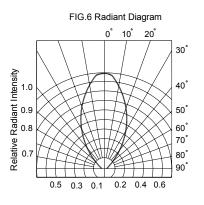






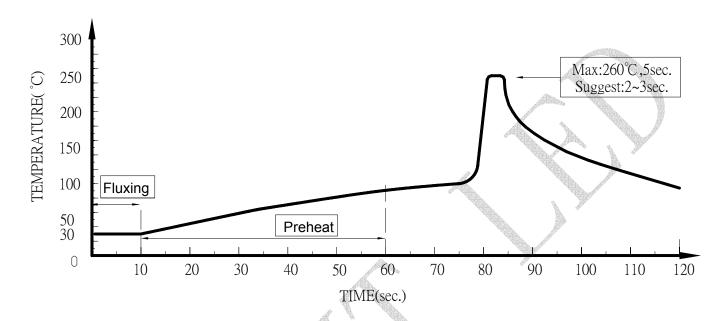






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Dip Soldering



- 1. Please avoid any external stress applied to the lead-frames and epoxy while the LEDs are at high temperature, especially during soldering
- 2. DIP soldering and hand soldering should not be done more than one time.
- 3. After soldering, avoid the epoxy lens from mechanical shock or vibration until the LEDs are back to room temerature.
- 4. Avoid rapid cooling during temperature ramp-down process
- 5. Although the soldering condition is recommended above, soldering at the lowest possible temperature is feasible for the LEDs

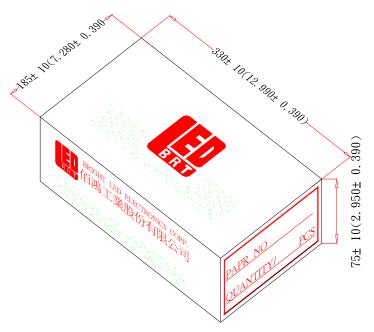
IRON Soldering

300℃ Within 3 sec.,One time only.

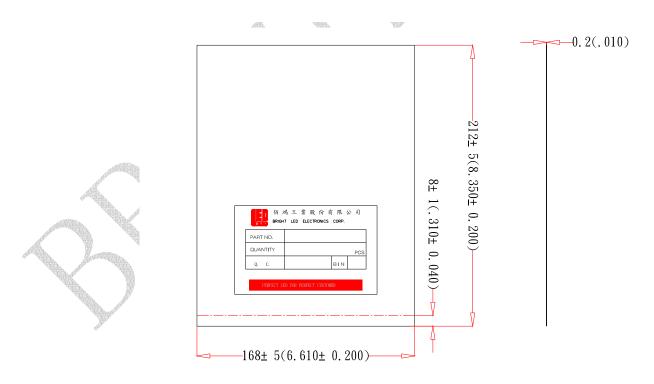


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Tapping and packaging specifications(Units: mm)



Packaging Bag Dimensions



Notes:

- 1 . 500pcs per bag, 5Kpcs per box.
- 2 · All dimensions are in millimeters(inches).
- 3 · Specifications are subject to change without notice.



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Infrared Emitting Diode Specification

Commodity: Infrared emitting diode

●Intensity Bin Limits (At 50mA)

BIN CODE	Min.(mW/sr)	Max.((mW/sr)
10J	7.07	9.90
11K	9.90	13.81
12L	13.81	19.42
13M	19.42	27.20
14N	27.20	38.08

NOTES: Tolerance of measurement of Radiant Intensity :±15%